YJ Planar Schottky Barrier Diode Die Specification

40V 0.2A,13mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB013L040AG-155A

Main Products Characterstics

- Average forward current: IF(AV) = 0.2 A
- Maximum operating junction temperature: Tj = 125 °C
- ESD rating: >2KV, per IEC61000-4-2 (Contact Discharge)
- Top metal: AL/3.915um

Maximum Ratings

Static Electrical Characteristics (Ta = 25°C)

I_F =20mA/200mA

Pulse Test: tp = 800 μs, δ ≤ 2%

Device Schematics and Outline Drawing

Die Thickness *
Die Size **
Top Metal Pad
Active Area
Top Metal
Back Metal
Steet width

Important Notice

Specification apply to die only. Actual performance may degor5R4(d) ra2C228(c)-4(o)9(n)28( )-snc buar5R.ce